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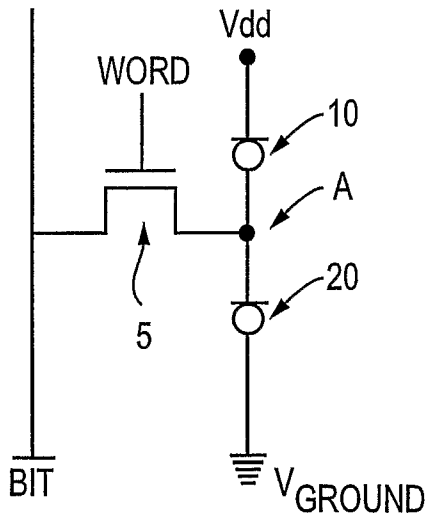
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(54) **Title:** STATIC RAM MEMORY CELL WITH DNR CHALCOGENIDE DEVICES AND METHOD OF FORMING



(57) **Abstract:** [0042] An SBAM memory device having improved stability including two series connected devices, at least one of the devices being a chalcogenide device exhibiting differential negative resistance characteristics. One of the two devices serves as the load of the other. A switch is provided to bias a middle input node and switch the memory device between two logic states.

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